

**Amendments to the Specification:**

After the title but before the first paragraph, please insert the following new paragraph:

**CROSS REFERENCE TO RELATED APPLICATIONS**

This application is National Stage filing under 35 U.S.C. § 371 of PCT International Application No. PCT/US03/32644 filed October 15, 2003 which claims the priority of U.S. Application No. 60/418,519 filed October 15, 2002, the disclosures of which are hereby incorporated by reference in their entirety.

On a separate page, page 19, please insert the following abstract:

**ATOMIC LAYER DEPOSITION OF NOBLE METALS****Abstract Of The Disclosure**

The present invention relates to ALD processes for deposition of a metal selected from Pd, Rh, Ru, Pt and Ir wherein a layer including the metal is formed on a surface composed of a material selected from W, Ta, Cu, Ni, Co, Fe, Mn, Cr, V Nb, tungsten nitride, tantalum nitride, titanium nitride, dielectrics and activated dielectrics at a temperature ranging from >60°C to <260°C. The layer is formed by sequentially pulsing into a chamber containing the surface a precursor for the metal and a reducing gas selected from hydrogen, glyoxylic acid, oxalic acid, formaldehyde, 2-propanol, imidazole and plasma-activated hydrogen.